

**Silicon NPN Power Transistor**

**BU208D**

**DESCRIPTION**

- High Voltage- $V_{CES} = 1500V(\text{Min.})$  ;
- Collector Current-  $I_C = 8.0A$
- Built-in Damper Diode

**APPLICATIONS**

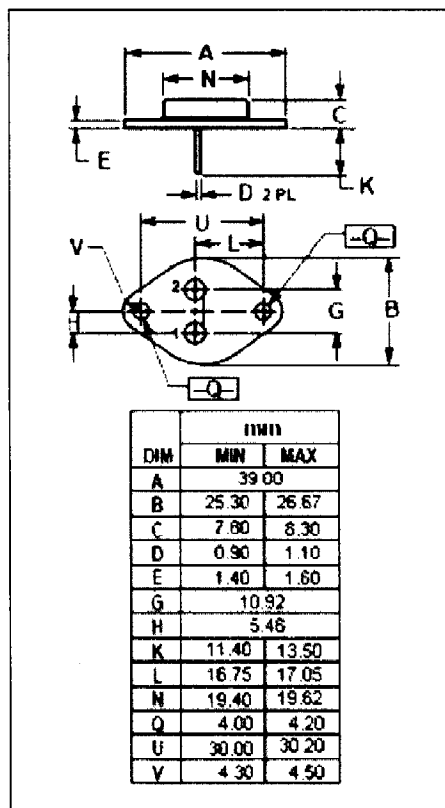
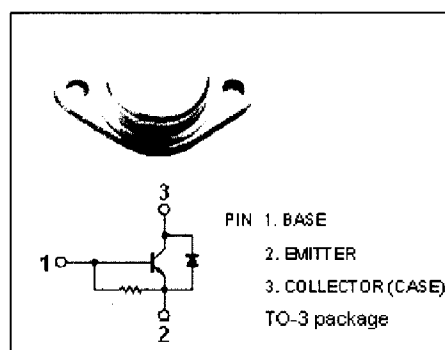
- Designed for use in large screen color deflection circuits .

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

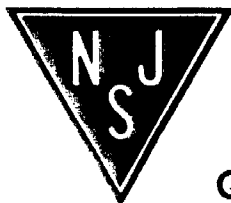
SYMBOL	PARAMETER	VALUE	UNIT
$V_{CES}$	Collector-Emitter Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	700	V
$V_{EBO}$	Emitter-Base Voltage	10	V
$I_C$	Collector Current-Continuous	8.0	A
$I_{CM}$	Collector Current-Peak	15	A
$P_C$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	150	W
$T_J$	Junction Temperature	175	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-65~175	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ\text{C/W}$



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## ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}; I_B=0$	700			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=4.5\text{A}; I_B=2\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=4.5\text{A}; I_B=2\text{A}$			1.3	V
$I_{CES}$	Collector Cutoff Current	$V_{CE}=1500\text{V}; V_{BE}=0$ $V_{CE}=1500\text{V}; V_{BE}=0; T_C=125^\circ\text{C}$			1.0 2.0	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5.0\text{V}; I_C=0$			300	mA
$h_{FE}$	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	8			
$f_T$	Current-Gain—Bandwidth Product	$I_C=0.1\text{A}; V_{CE}=5\text{V}; f_{test}=5\text{MHz}$		7		MHz
$V_{ECF}$	C-E Diode Forward Voltage	$I_F=4\text{A}$			2	V

### Switching Times( Inductive load)

$t_s$	Storage Time	$I_C=4.5\text{A}; I_B=1.8\text{A}; L_B=3\mu\text{H};$ $V_{CC}=140\text{V}, L_C=0.9\text{mH}$		7		$\mu\text{s}$
$t_f$	Fall Time			0.55		$\mu\text{s}$